

Abstract of the Disclosure

Provided is a method of depositing a thin film on a wafer using an aluminum compound. The method includes (S1) mounting the wafer on the wafer block; and (S2) depositing an Al_2O_3 thin film. Step (S2) includes (S2-1) feeding ozone by spraying ozone through the first spray holes and spraying an inert gas through the second spray holes; (S2-2) purging the ozone by stopping the spraying of the ozone, spraying the inert gas through the first spray holes, and spraying the same inert gas as in step (S2-1) through the second spray holes; (S2-3) feeding TMA by spraying the TMA, which is transferred by a carried gas, through the second spray holes and spraying the inert gas through the first spray holes; and (S2-4) purging the TMA by stopping the spraying of the TMA, spraying the same carrier gas as in step (S2-3) through the second spray holes, and spraying the same inert gas as in step (S2-3) through the first spray holes. Step (S2) is performed by repeating an ALD cycle of steps (S2-1), (S2-2), (S2-3), and (S2-4) twice or more.